

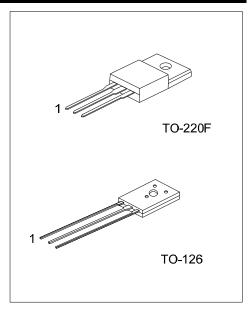
2SC4793

NPN SILICON TRANSISTOR

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FEATURES

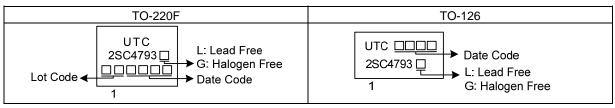
*High transition frequency *Power amplifier applications *Driver stage amplifier applications



ORDERING INFORMATION

Order Number		Dookogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
2SC4793L-x-TF3-T	2SC4793G-x-TF3-T	TO-220F	В	С	Е	Tube	
2SC4793L-x-T60-K	2SC4793G-x-T60-K	TO-126	E C		В	Bulk	
Note: Pin Assignment: B: Bas	Note: Pin Assignment: B: Base C: Collector E: Emitter						
2SC4793G-x-TF3-T (1)Packing Type (2)Package Type (3)Rank (4)Green Package		(1) T: Tube, K: Bulk (2) TF3: TO-220F, T60: TO-126 (3) refer to Classification of h _{FE} (4) G: Halogen Free and Lead Free, L: Lead Free					

MARKING



■ **ABSOLUTE MAXIMUM RATINGS** (T_A=25°C, unless others specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Collector-Base Voltage		V _{CBO}	230	V	
Collector-Emitter Voltage		V _{CEO}	230	V	
Emitter-Base Voltage		V _{EBO}	5	V	
Collector Current		Ιc	1	А	
Base Current		I _B	0.1	А	
Collector Power Dissipation	T _A =25°C	TO-220F	Pc	2.0	W
		TO-126		1.4	W
	$T_{c}=25^{\circ}C$	TO-220F		20	W
		TO-126		16	W
Junction Temperature		ΤJ	+150	°C	
Storage Temperature Range		T _{STG}	-55 ~ +150	°C	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless others specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =10mA, I _B =0	230			V
Base -Emitter Voltage	V _{BE}	V _{CE} =5V, I _C =500mA			1.0	V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =500mA, I _B =50mA			1.5	V
Collector Cut-off Current	I _{CBO}	V _{CB} =230V, I _E =0			1.0	μA
Emitter Cut-off Current	I _{EBO}	V _{EB} =5V, I _C =0			1.0	μA
DC Current Gain	h _{FE}	V _{CE} =5V, I _C =100mA	100		320	
Transition Frequency	f⊤	V _{CE} =10V, I _C =100mA		100		MHz
Collector Output Capacitance	Cob	V _{CB} =10V, I _E =0, f=1MHz		20		рF

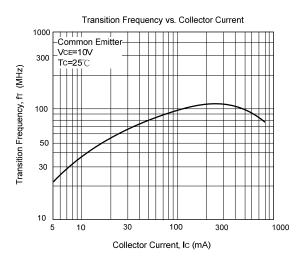
CLASSIFICATION OF h_{FE}

RANK	А	В
RANGE	100-200	180-320

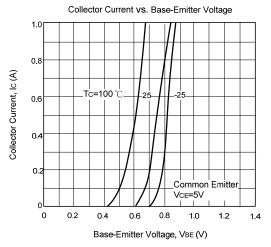


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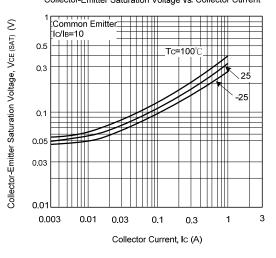
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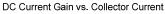


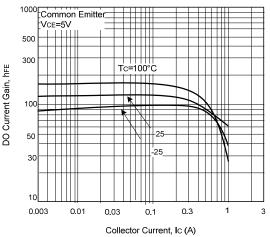
TYPICAL CHARACTERISTICS

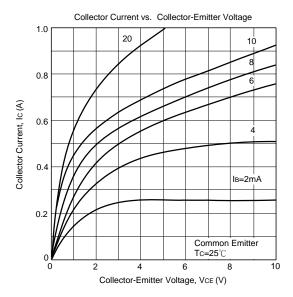


Collector-Emitter Saturation Voltage vs. Collector Current

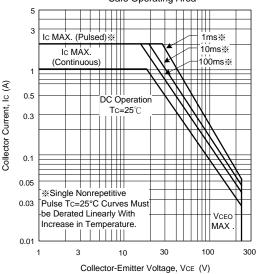














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